P-Channel 20 V (D-S) MOSFET

MOSFET PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
- 20	0.112 at V_{GS} = - 4.5 V	- 3.1	3.3 nC
	0.142 at V_{GS} = - 2.5 V	- 2.7	

FEATURES

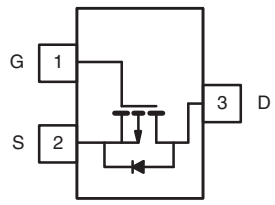
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Load Switch

TO-236 (SOT-23)



Top View
Si2301CDS (N1)*
* Marking Code

Ordering Information: Si2301CDS-T1-E3 (Lead (Pb)-free)
Si2301CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 20	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 3.1	A
	T_C = 70 °C		- 2.5	
	T_A = 25 °C		- 2.3[b, c]	
	T_A = 70 °C		- 1.8[b, c]	
Pulsed Drain Current		I_{DM}	- 10	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 1.3	
	T_A = 25 °C		- 0.72[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	1.6	W
	T_C = 70 °C		1.0	
	T_A = 25 °C		0.86[b, c]	
	T_A = 70 °C		0.55[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, d]	≤ 5 s	R_{thJA}	120	145	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	62	78	

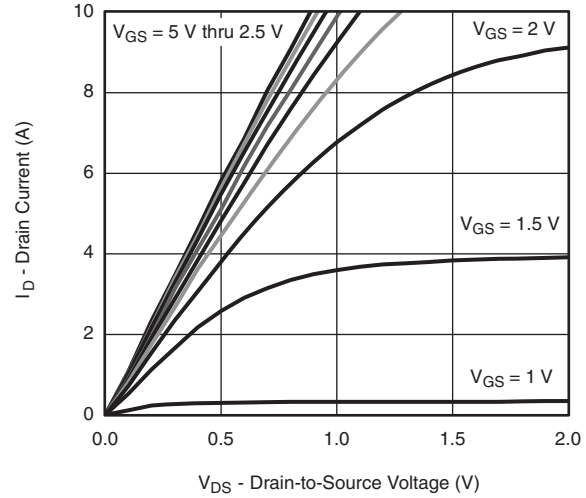
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. Maximum under steady state conditions is 175 °C/W.

MOSFET SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 18		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.4		- 1	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 6			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 2.8 A		0.090	0.112	Ω
		V_{GS} = - 2.5 V, I_D = - 2.0 A		0.110	0.142	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 5 V, I_D = - 2.8 A		9.5		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 10 V, V_{GS} = 0 V, f = 1 MHz		405		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer Capacitance	C_{rss}			55		
Total Gate Charge	Q_g	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 3 A		5.5	10	nC
		V_{DS} = - 10 V, V_{GS} = - 2.5 V, I_D = - 3 A		3.3	6	
Gate-Source Charge	Q_{gs}			0.7		
Gate-Drain Charge	Q_{gd}			1.3		
Gate Resistance	R_g	f = 1 MHz		6.0		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 10 Ω I_D = - 1 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		11	20	ns
Rise Time	t_r			35	60	
Turn-Off Delay Time	$t_{d(off)}$			30	50	
Fall Time	t_f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 1.3	A
Pulse Diode Forward Current[a]	I_{SM}				- 10	
Body Diode Voltage	V_{SD}	I_S = - 0.7 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 3.0 A, dI/dt = 100 A/µs, T_J = 25 °C		30	50	ns
Body Diode Reverse Recovery Charge	Q_{rr}			25	50	nC
Reverse Recovery Fall Time	t_a			15		ns
Reverse Recovery Rise Time	t_b			15		

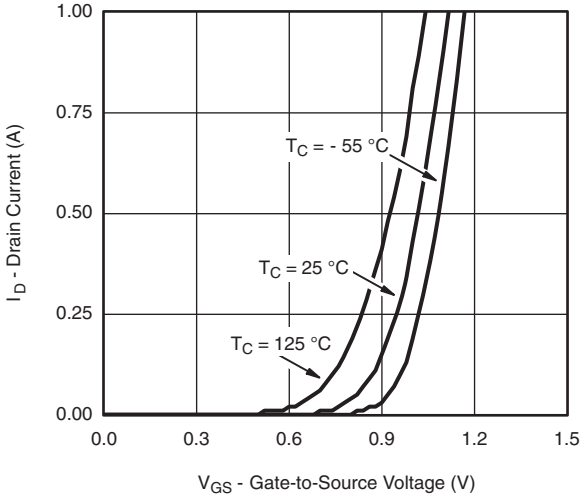
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

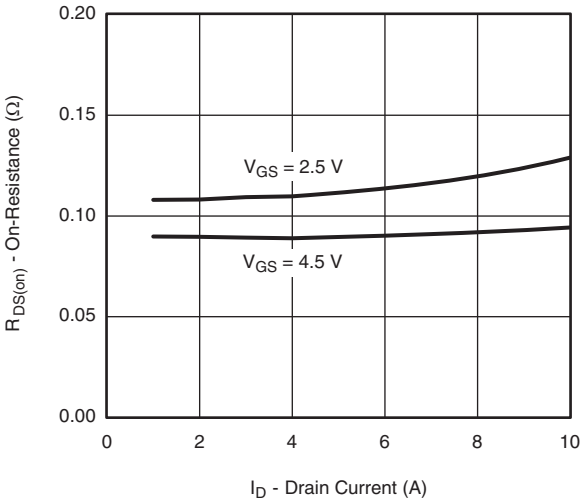
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



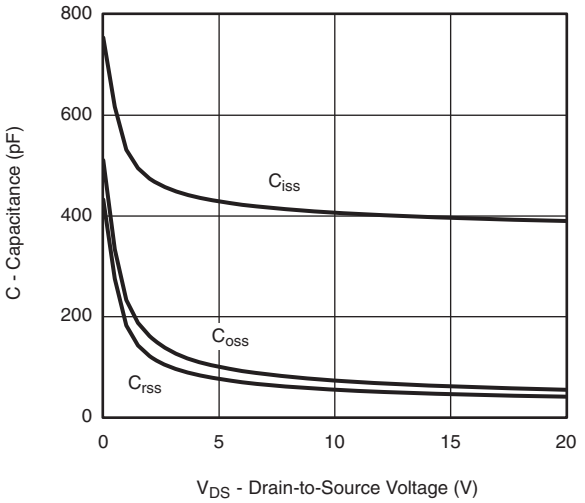
Output Characteristics



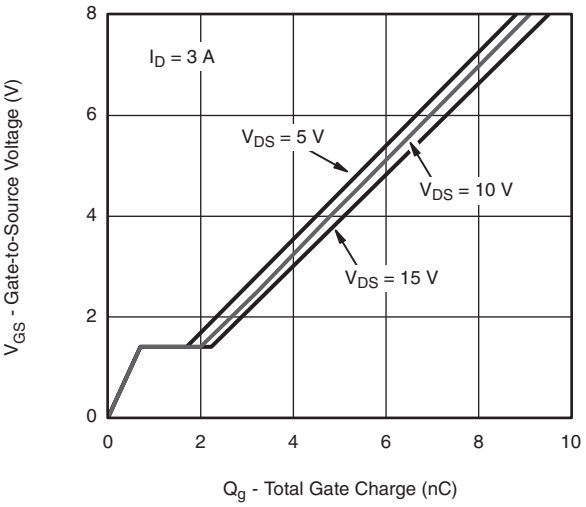
Transfer Characteristics



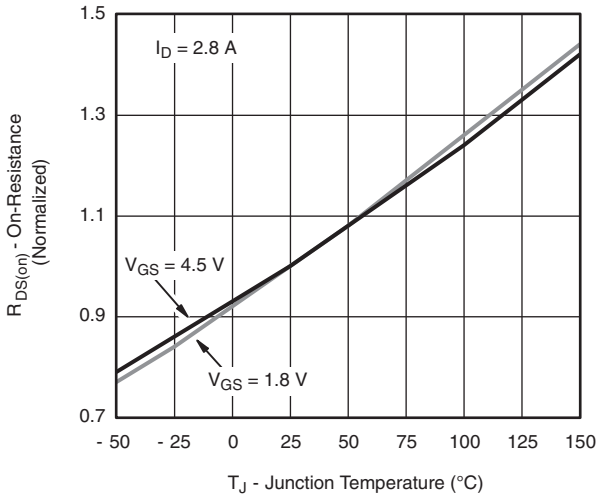
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

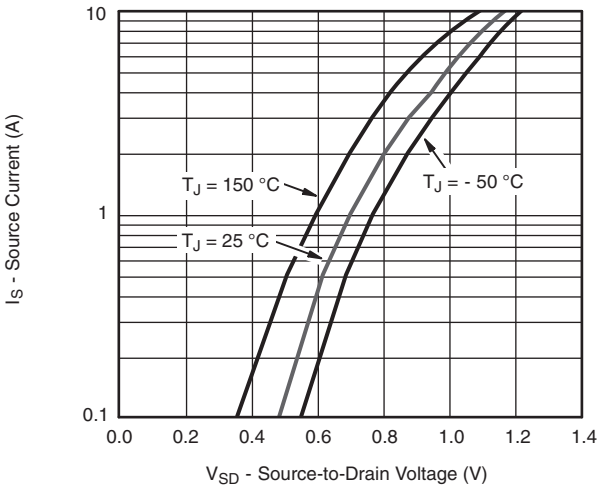


Gate Charge

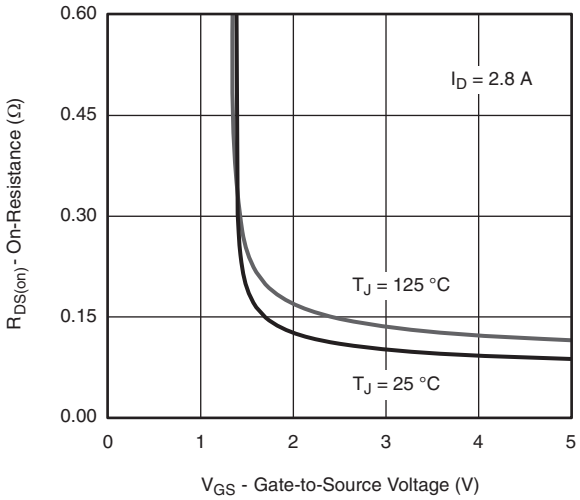


On-Resistance vs. Junction Temperature

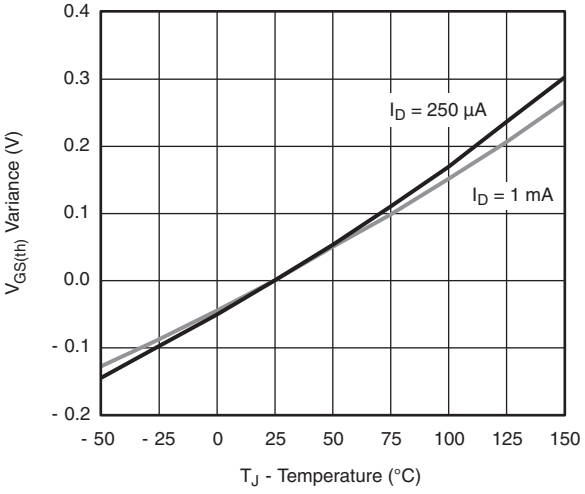
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



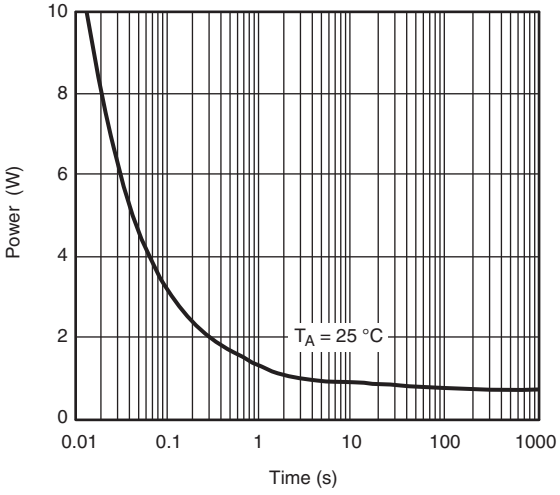
Source-Drain Diode Forward Voltage



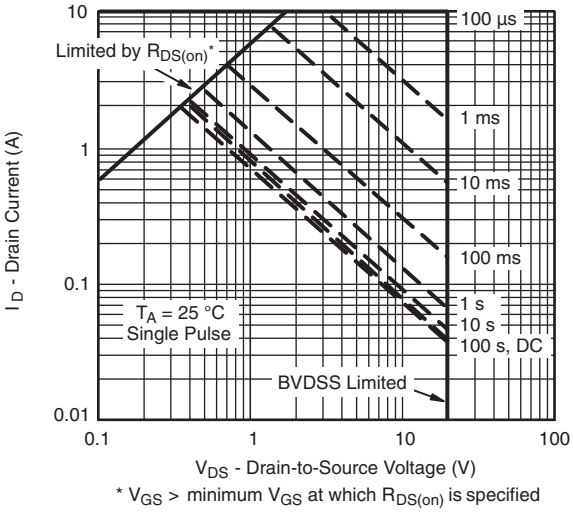
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



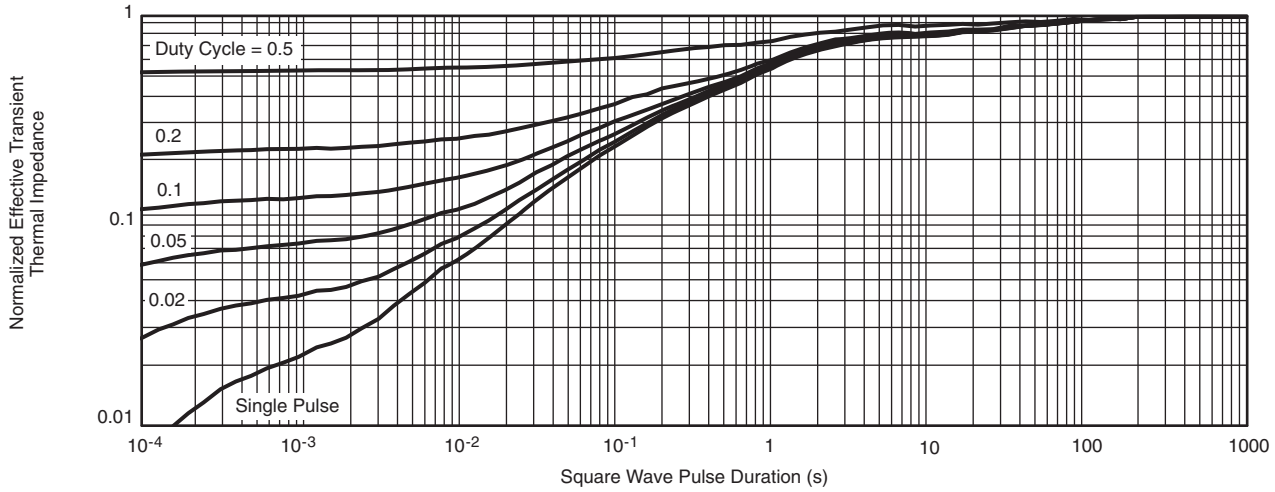
Single Pulse Power



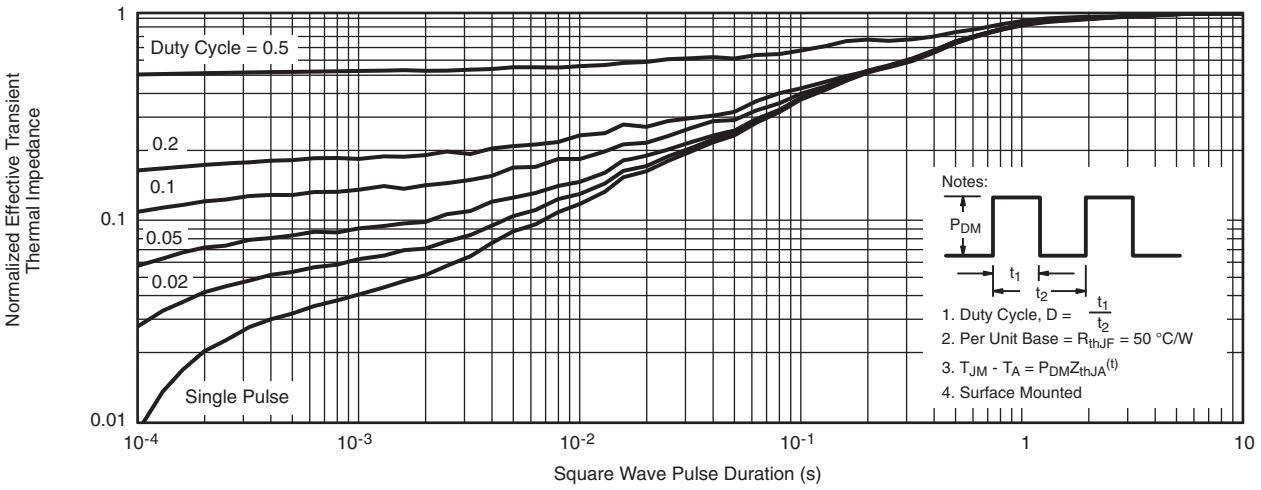
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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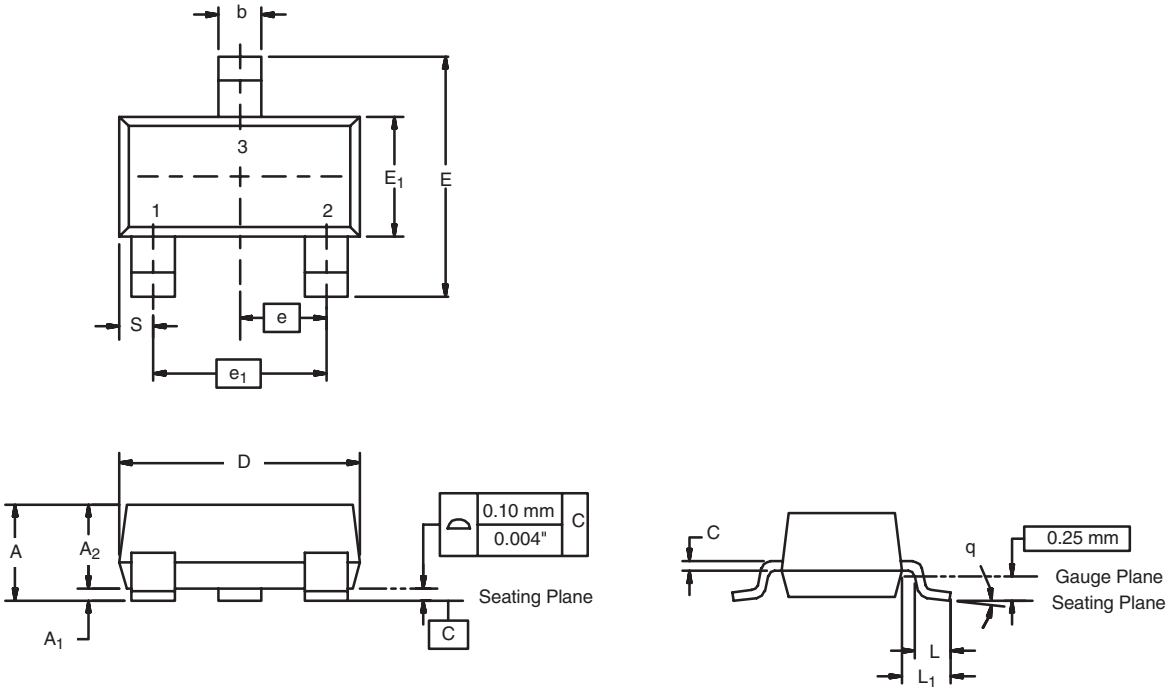
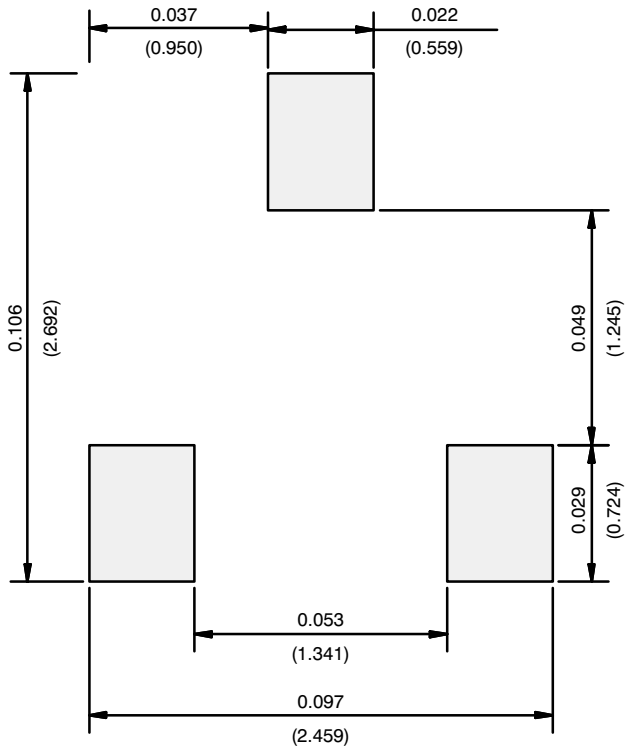
SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A_1	0.01	0.10	0.0004	0.004
A_2	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E_1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e_1	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L_1	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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